## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

METHOD OF FABRICATING A CMOS DEVICE WITH DUAL METAL GATE ELECTRODES

Application Number: 10/826665

Confirmation Number: 9608

First Named Applicant: CHANG PARK
Attorney Docket Number: 61472-0308425

Art Unit: Examiner:

Search string: (6653698 or 6352913).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6653698	2003-11-25	LEE ET AL.	B2	257	407
	2	6352913	2002-03-05	MISTRY ET AL.	B1	438	587

## **Signature**

Examiner Name	Date